/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

/ Features

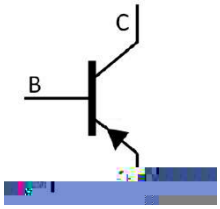
, 2SD1781K

Low VCE(sat),complements the 2SD1781K.

/ Applications

Low frequency amplifier applications.

/ Equivalent Circuit



/ Pinning

PIN1 Base PIN 2 Emitter PIN 3 Collector

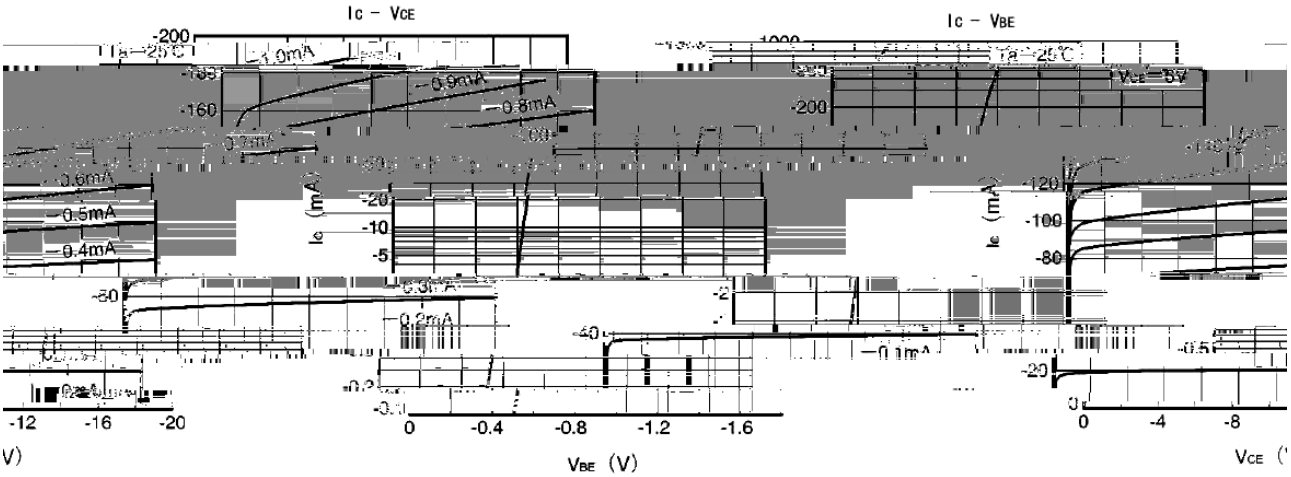
/ h_{FE} Classifications & Marking

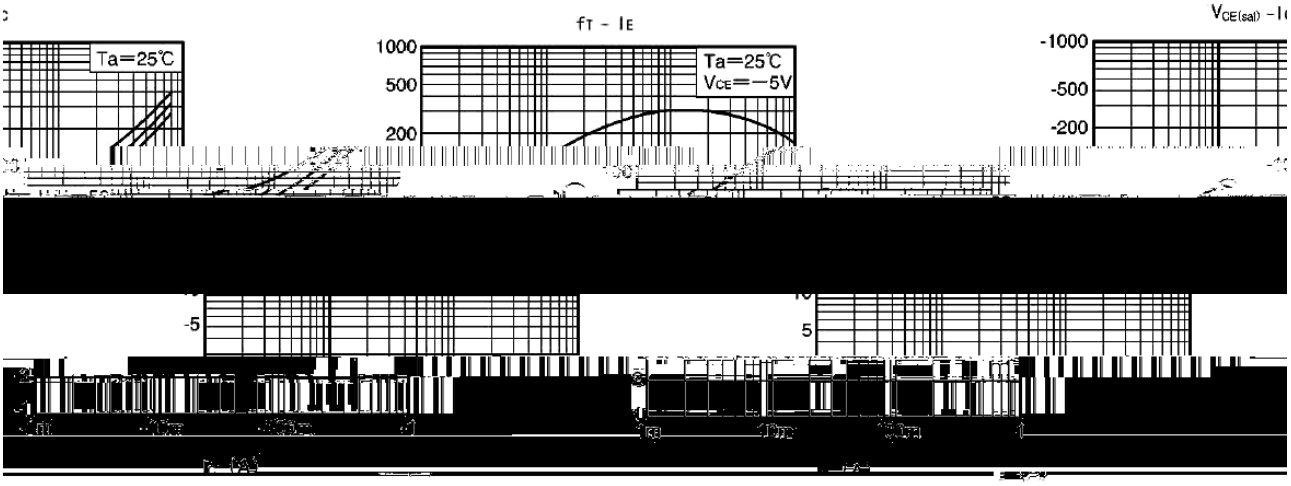
h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120 270	180 390
Marking	HAHQ	HAHR

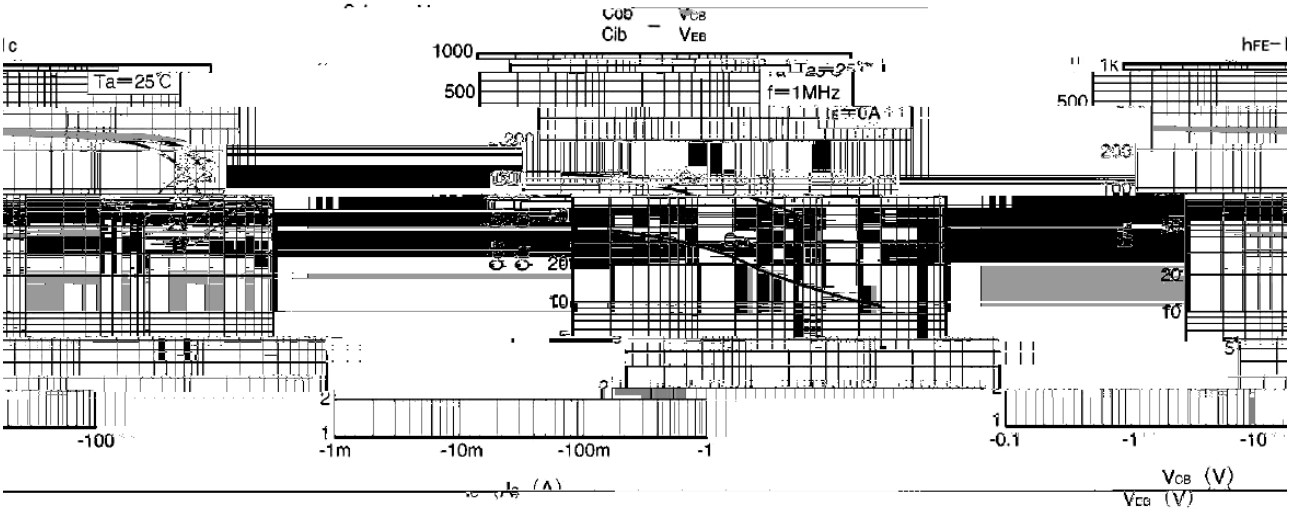
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V_{CBO}	I_C =-50 A	-40			V
Collector-Emitter Breakdown Voltage	V_{CEO}	I_C =-1.0mA	-32			V
Emitter-Base Breakdown Voltage	V_{EBO}	I_E=-50 A	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-20V I_E=0			-0.5	A
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=(anticque)3.47(ncy 0 73918.(f38.5545.0204 Tm -0.0915 2 I_C=0			-0.5	A
DC Current Gain	h_{FE}	V_{CE}=-3.0V I_C=-100mA	120		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_c I				

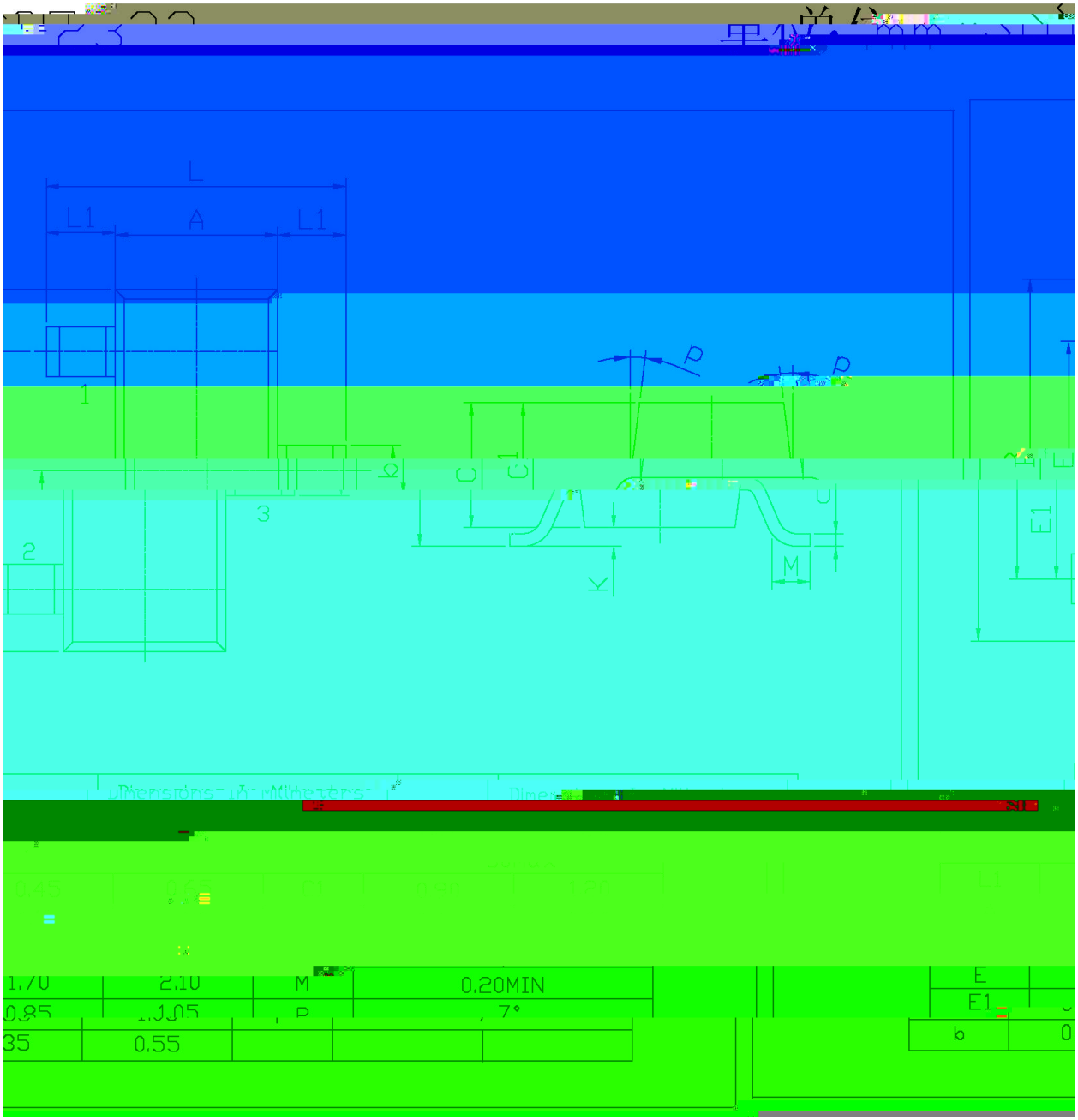
/ Electrical Characteristic Curve







/ Package Dimensions



/ Marking Instructions

H

AH

Q: h_{FE}

Note:

H: Company Code

AH: Product Type Code

Q: h_{FE} Classifications Symbol Code

( ) / Temperature Profile for IR Reflow Soldering(Pb [